AMENDMENTS TO THE CLAIMS:

This listing of claims will replace all prior versions and listings of claims in the application:

1. (Currently Amended) A computer implemented method for development profile simulation comprising:

preparing an actual dissolution rate of a photosensitive resist developed by a developer, the actual dissolution rate being measured outside a computer;

calculating optical intensities in [[a]] the photosensitive resist;

calculating a spatial average value of the optical intensities;

reading calculating a measured changing ratio of [[a]] the measured dissolution rate of the photosensitive resist relating to an alkaline concentration changed by of the developer, depending on at least one of exposure dose on the photosensitive resist, a position in [[the]] a thickness direction of the photosensitive resist and [[an]] the alkaline concentration of the developer for the photosensitive resist;

obtaining a calculated dissolution rate by using the spatial average value and the measured changing ratio; [[and]]

predicting a pattern shape of the photosensitive resist from the calculated dissolution rate:

and

storing the predicted pattern shape in a memory,

wherein the changing ratio is calculated from a logarithm of the measured dissolution rate to the alkaline concentration.

- 2. (Currently Amended) The method of claim 1, wherein the optical intensities is an are aerial image intensity intensities.
- 3. (Currently Amended) The method of claim 1, wherein <u>each of</u> the optical intensities <u>is concentration</u> are concentrations of photoreaction products.
 - 4. (Canceled)

<u>and</u>

5. (Currently Amended) The method of claim 1, A method for development of a profile simulation comprising:

preparing an actual dissolution rate of a photosensitive resist developed by a developer, the actual dissolution rate being measured outside a computer;

calculating optical intensities in the photosensitive resist;

calculating a spatial average value of the optical intensities;

concentration of the developer, depending on at least one of exposure dose on the photosensitive resist, a position in a thickness direction of the photosensitive resist and the alkaline concentration of the developer;

obtaining a calculated dissolution rate by using the spatial value and the changing ratio; predicting a pattern shape of the photosensitive resist from the calculated dissolution rate;

storing the predicted pattern shape in a memory,

wherein the measured changing ratio of the dissolution rate is calculated from a logarithm of [[a]] the measured dissolution rate to a logarithm of the alkaline concentration.

- 6. (Currently Amended) The method of claim 1, wherein the spatial average value is calculated in [[an]] a part of a whole exposed area where the photosensitive resist is exposed in a certain amount or more and dissolves in an initial stage of development.
- 7. (Currently Amended) The method of claim 1, wherein the spatial average <u>value</u> is calculated in reference positions moving along development time, which is different from of the photosensitive resist when the developer flows on the photosensitive resist, the reference <u>positions being located upstream of</u> the position where the pattern shape of the photosensitive resist is predicted.
- 8. (Currently Amended) A computer-implemented method for development profile simulation comprising:

preparing an actual dissolution rate of a photosensitive resist developed by a developer, the actual dissolution rate being measured outside a computer;

calculating optical intensities in [[a]] the photosensitive resist;

calculating a spatial average value of the optical intensities;

obtaining calculating a changing ratio of a logarithm of [[a]] the measured dissolution rate to an alkaline concentration of the developer for the photosensitive resist or the changing ratio of the logarithm of the measured dissolution rate to a logarithm of the alkaline concentration of the developer for the photosensitive resist;

obtaining a calculated dissolution rate by using the spatial average value and the ealeulated changing ratio of the logarithm of the measured dissolution rate to the alkaline concentration of [[a]] the developer or the ealeulated changing ratio of the logarithm of the measured dissolution rate to the logarithm of [[an]] the alkaline concentration of the developer; [[and]]

predicting a pattern shape of the photosensitive resist by using the calculated dissolution rate; and

storing the predicted pattern shape in a memory.

- 9. (Currently Amended) The method of claim 8, wherein the optical intensities is an are aerial image intensities.
- 10. (Currently Amended) The method of claim 8, wherein the optical intensities is eoncentration are concentrations of photoreaction products.
- 11. (Currently Amended) The method of claim 8, wherein the spatial average value is calculated in [[an]] a part of a whole exposed area where the photosensitive resist is exposed in a certain amount or more and dissolves in an initial stage of development.
- 12. (Currently Amended) The method of claim 8, wherein the spatial average <u>value</u> is calculated in reference positions <u>of the photosensitive resist</u> when the <u>developer flows on the photosensitive resist</u>, the reference positions being located upstream of <u>moving along</u>

development time, which is different from the position where the pattern shape of the photosensitive resist is predicted.

13. (Currently Amended) A computer implemented method for development profile simulation comprising:

preparing an actual dissolution rate of a photosensitive resist developed by a developer, the actual dissolution rate being measured outside a computer;

calculating optical intensities in [[a]] the photosensitive resist;

calculating a spatial average value of the optical intensities in [[an]] a part of a whole exposed area where the photosensitive resist is exposed in a certain amount or more and dissolves in an initial stage of development;

reading <u>calculating</u> a <u>measured</u> changing ratio of [[a]] <u>the measured</u> dissolution rate of the photosensitive resist relating to an alkaline concentration <u>of the developer</u>;

obtaining a calculated dissolution rate by using the spatial average value and the measured changing ratio; [[and]]

predicting a pattern shape of the photosensitive resist by using the calculated dissolution rate; and

storing the predicted pattern shape in a memory.

14. (Currently Amended) The method of claim 13, wherein the optical intensities is an are aerial image intensity intensities.

- 15. (Currently Amended) The method of claim 13, wherein the optical intensities is eoncentration are concentrations of photoreaction products.
- 16. (Currently Amended) The method of claim 13, wherein the measured changing ratio of the dissolution rate is calculated from [[a]] the logarithm of a measured dissolution rate to the alkaline concentration.
- 17. (Currently Amended) The method of claim 13, wherein the measured changing ratio of the dissolution rate is calculated from a logarithm of [[a]] the measured dissolution rate to a logarithm of the alkaline concentration.
- 18. (Currently Amended) The method of claim 13, wherein the spatial average <u>value</u> is calculated in reference positions <u>of the photosensitive resist when the developer flows on the photosensitive resist, the reference positions being located upstream of moving along development time, which is different from the position where the pattern shape of the photosensitive resist is predicted.</u>
- 19. (Currently Amended) A computer implemented method for development profile simulation comprising:

preparing an actual dissolution rate of a photosensitive resist developed by a developer, the actual dissolution rate being measured outside a computer;

calculating optical intensities in a target position to predict a pattern shape of [[a]] the photosensitive resist and in reference positions of the photosensitive resist, the reference

photosensitive resist moving along development time;

calculating spatial average values of the optical intensities in the reference positions;

reading calculating a measured changing ratio of [[a]] the measured dissolution rate of
the photosensitive resist relating to [[the]] an alkaline concentration of the developer;

obtaining calculated dissolution rates by using the spatial average values in the reference positions and the measured changing ratio; [[and]]

predicting the pattern shape of the photosensitive resist in the target position by using the calculated dissolution rates and the optical intensities in the target position; and storing the predicted pattern shape in a memory.

- 20. (Currently Amended) The method of claim 19, wherein the optical intensities is an are aerial image intensity intensities.
- 21. (Currently Amended) The method of claim 19, wherein the optical intensities [[is]] are concentration concentrations of photoreaction products.
- 22. (Currently Amended) The method of claim 19, wherein the measured changing ratio of the dissolution rate is calculated from a logarithm of [[a]] the measured dissolution rate to the alkaline concentration.

- 23. (Currently Amended) The method of claim 19, wherein the measured changing ratio of the dissolution rate is calculated from a logarithm of [[a]] the measured dissolution rate to a logarithm of the alkaline concentration.
- 24. (Currently Amended) The method of claim 19, wherein the spatial average value is calculated in [[an]] a part of a whole exposed area where the photosensitive resist is exposed in a certain amount or more and dissolves in an initial stage of development.
- 25. (Currently Amended) A computer program product for controlling a computer system so as to simulate <u>a</u> development profile, the computer program product comprising:

 <u>a recording medium readable by the computer system;</u>

instructions recorded on the recording medium for directing the computer system to

prepare an actual dissolution rate of a photosensitive resist developed by a developer, the actual dissolution rate being measured outside the computer system;

instructions configured recorded on the recording medium for directing the computer system to calculate optical intensities in [[a]] the photosensitive resist within the computer system;

instructions configured recorded on the recording medium for directing the computer system to calculate a spatial average value of the optical intensities within the computer system;

instructions configured recorded on the recording medium for directing the computer

system to read calculate a measured changing ratio of [[a]] the measured dissolution rate of the photosensitive resist relating to an alkaline concentration changed by of the developer,

depending on at least one of exposure dose on the photosensitive resist, a position in [[the]] a

thickness direction of the photosensitive resist and [[an]] the alkaline concentration of the developer for the photosensitive resist within the computer system;

instructions eonfigured recorded on the recording medium for directing the computer system to obtain a calculated dissolution rate by using the spatial average value and the measured changing ratio within the computer system; [[and]]

instructions configured recorded on the recording medium for directing the computer system to predict a pattern shape of the photosensitive resist from the calculated dissolution rate within the computer system; and

instructions recorded on the recording medium for directing the computer system to store
the predicted pattern shape in a memory,

wherein the changing ratio is calculated from a logarithm of the measured dissolution rate to the alkaline concentration.

26. (Currently Amended) A computer program product for controlling a computer system so as to simulate <u>a</u> development profile, the computer program product comprising:

<u>a recording medium readable by the computer system;</u>

instructions recorded on the recording medium for directing the computer system to

prepare an actual dissolution rate of a photosensitive resist developed by a developer, the actual dissolution rate being measured outside the computer system;

instructions configured recorded on the recording medium for directing the computer system to calculate optical intensities in [[a]] the photosensitive resist within the computer system;

instruction configured instructions recorded on the recording medium for directing the computer system to calculate a spatial average value of the optical intensities within the computer system;

instruction configured instructions recorded on the recording medium for directing the computer system to obtain calculate a changing ratio of a logarithm of a measured dissolution rate to an alkaline concentration of the developer for the photosensitive resist or the changing ratio of the logarithm of the measured dissolution rate to a logarithm of the alkaline concentration of the developer for the photosensitive resist within the computer system;

instruction configured instructions recorded on the recording medium for directing the computer system to obtain a calculated dissolution rate by using the spatial average value and the calculated changing ratio of the logarithm of the measured dissolution rate to the alkaline concentration of the developer or the calculated changing ratio of the logarithm of the measured dissolution rate to the logarithm of the alkaline concentration of the developer within the computer system; and

instruction configured instructions recorded on the recording medium for directing the computer system to predict a pattern shape of the photosensitive resist by using the calculated dissolution rate within the computer system; and

instructions recorded on the recording medium for directing the computer system to store the predicted pattern shape in a memory.

27. (Currently Amended) A computer program product for controlling a computer system so as to simulate <u>a</u> development profile, the computer program product comprising: <u>a recording medium readable by the computer system;</u>

instructions recorded on the recording medium for directing the computer system to

prepare an actual dissolution rate of a photosensitive resist developed by a developer, the actual

dissolution rate being measured outside the computer system;

instruction configured instructions recorded on the recording medium for directing the computer system to calculate optical intensities in [[a]] the photosensitive resist within the computer system;

instruction configured instructions recorded on the recording medium for directing the computer system to calculate a spatial average value of optical intensities in [[an]] a part of a whole exposed area where the photosensitive resist is exposed in a certain amount or more and dissolves in an initial stage of development within the computer system;

instruction configured instructions recorded on the recording medium for directing the computer system to [[read]] calculate a measured changing ratio of [[a]] the measured dissolution rate of the photosensitive resist relating to an alkaline concentration of the developer within the computer system;

<u>instruction configured</u> <u>instructions recorded on the recording medium for directing the</u>

<u>computer system</u> to obtain a calculated dissolution rate by using the spatial average value and the

<u>measured</u> changing ratio <u>within the computer system</u>; [[and]]

instruction configured instructions recorded on the recording medium for directing the computer system to predict a pattern shape of the photosensitive resist by using the calculated dissolution rate-within the computer system; and

instructions recorded on the recording medium for directing the computer system to store
the predicted pattern shape in a memory.

28. (Currently Amended) A computer program product for controlling a computer system so as to simulate <u>a</u> development profile, the computer program product comprising: <u>a recording medium readable by the computer system;</u>

instructions recorded on the recording medium for directing the computer system to

prepare an actual dissolution rate of a photosensitive resist developed by a developer, the actual dissolution rate being measured outside the computer system;

instruction configured instructions recorded on the recording medium for directing the computer system to calculate optical intensities in a target position to predict a pattern shape of [[a]] the photosensitive resist and in reference positions of the photosensitive resist, the reference positions being located upstream of the target position when the developer flows on the photosensitive resist moving along development time within the computer system;

instruction configured instructions recorded on the recording medium for directing the computer system to calculate spatial average values of the optical intensities in the reference positions within the computer system;

instruction configured instructions recorded on the recording medium for directing the computer system to read calculate a measured changing ratio of [[a]] the measured dissolution rate of the photosensitive resist relating to the an alkaline concentration within the computer-system of the developer;

instruction configured instructions recorded on the recording medium for directing the computer system to obtain calculated dissolution rates by using the spatial average values in the reference positions and the measured changing ratio within the computer system; [[and]]

instruction configured instructions recorded on the recording medium for directing the computer system to predict the pattern shape of the photosensitive resist in the target position by

using the calculated dissolution rates and the optical intensities in the target position within the computer system; and

instructions recorded on the recording medium for directing the computer system to store the predicted pattern shape in a memory.

29. (Currently Amended) A computer implemented method for mask pattern data correction comprising:

preparing an actual dissolution rate of a photosensitive resist developed by a developer, the actual dissolution rate being measured outside a computer;

reading a designed pattern data in [[a]] the photosensitive resist[[,]] and a mask pattern data[[,]]; [[and]]

calculating a measured changing ratio of [[a]] the measured dissolution rate of the photosensitive resist relating to an alkaline concentration of the developer, depending on changed by at least one of exposure dose on the photosensitive resist, a position in the thickness direction of the photosensitive resist and an alkaline concentration of the developer for the photosensitive resist;

calculating optical intensities in the photosensitive resist by using the mask pattern data; calculating a spatial average value of the optical intensities;

obtaining a calculated dissolution rate by using the spatial average value and the measured changing ratio;

predicting a pattern shape of the photosensitive resist from the calculated dissolution rate; [[and]]

optimizing the mask pattern data so as to make the calculated pattern shape similar to the designed pattern data in the photosensitive resist; and

storing the optimized mask pattern data in a memory,

wherein the changing ratio is calculated from a logarithm of the measured dissolution rate to the alkaline concentration.

30. (Currently Amended) A computer implemented method for mask pattern data correction comprising:

preparing an actual dissolution rate of a photosensitive resist developed by a developer, the actual dissolution rate being measured outside a computer;

obtaining a designed pattern data in [[a]] the photosensitive resist[[,]] and a mask pattern data[[,]]; and a calculated

calculating a changing ratio of a logarithm of [[a]] the measured dissolution rate to an alkaline concentration of the developer for the photosensitive resist or the ealculated changing ratio of the logarithm of the measured dissolution rate to a logarithm of the alkaline concentration of the developer for the photosensitive resist;

calculating optical intensities in the photosensitive resist by using the mask pattern data; calculating a spatial average value of the optical intensities;

obtaining a calculated dissolution rate by using the spatial average value and the measured changing ratio;

predicting a pattern shape of the photosensitive resist from the calculated dissolution rate; [[and]]

optimizing the mask pattern data so as to make the calculated pattern shape similar to the designed pattern data in the photosensitive resist; and

storing the optimized mask pattern data in a memory.

31. (Currently Amended) A computer implemented method for mask pattern data correction comprising:

preparing an actual dissolution rate of a photosensitive resist developed by a developer, the actual dissolution rate being measured outside a computer;

reading a designed pattern data in [[a]] the photosensitive resist[[,]] and a mask pattern data; , and

calculating a measured changing ratio of [[a]] the measured dissolution rate of the photosensitive resist relating to an alkaline concentration of the developer;

calculating optical intensities in the photosensitive resist by using the mask pattern data; calculating a spatial average value of optical intensities in [[an]] a part of a whole exposed area where the photosensitive resist is exposed in a certain amount or more and dissolves in an initial stage of development;

obtaining a calculated dissolution rate by using the spatial average value and the measured changing ratio;

predicting a pattern shape of the photosensitive resist from the calculated dissolution rate;
[[and]]

optimizing the mask pattern data so as to make the calculated pattern shape similar to the designed pattern data in the photosensitive resist; and

storing the optimized mask pattern data in a memory.

32. (Currently Amended) A computer implemented method for mask pattern data correction comprising:

preparing an actual dissolution rate of a photosensitive resist developed by a developer, the actual dissolution rate being measured outside a computer;

reading a designed pattern data in [[a]] the photosensitive resist[[,]] and a mask pattern data; [[, and]]

calculating a measured changing ratio of [[a]] the measured dissolution rate of the photosensitive resist relating to the spatial average value an alkaline concentration of the developer;

reference positions of the photosensitive resist moving along development time by using the mask pattern data, the reference positions being located upstream of the target position when the developer flows on the photosensitive resist moving along development time;

calculating a spatial average value of the optical intensities in the reference positions; obtaining a calculated dissolution rate by using the spatial average value in the reference positions and the measured changing ratio;

predicting a pattern shape of the photosensitive resist by using the calculated dissolution rate and the optical intensities in the target position; [[and]]

optimizing the mask pattern data so as to make the calculated pattern shape similar to the designed pattern data in the photosensitive resist; and

storing the optimized mask pattern data in a memory.